



LI DE HENG ELECTRONICS SD101AW /SD101BW /SD101CW

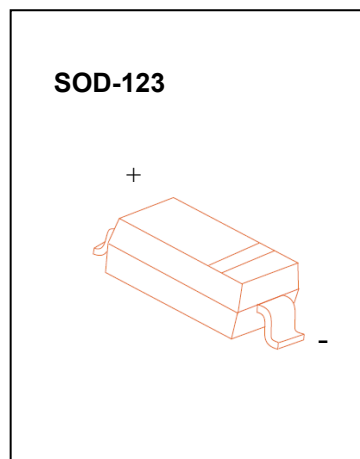
SOD-123 Plastic-Encapsulate Diodes

SD101AW /SD101BW /SD101CW

SCHOTTKY DIODES

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time



Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C

| Parameter Symbol | | SD101AW SD10 | 1BW | SD101CW | Unit |
|--|------------------------------------|--------------|-----|---------|---------|
| Peak Repetitive Peak reverse voltage | V _{RRM} | 60 | 50 | 40 | V |
| Working Peak DC Blocking Voltage | V _{RWM} V _R | | | | |
| RMS Reverse Voltage | V _{R(RMS)} | 42 | 35 | 28 | V |
| Forward Continuous Current | I _{FM} | 15 | | | mA |
| Repetitive Peak Forward Current @t<1.0s @t=10μs | I _{FRM} | 50 2.0 | | | mA A |
| Power Dissipation | P _d | 500 | | | mW |
| Thermal Resistance Junction to Ambient | R _{θJA} | 250 | | | °C/W |
| Storage temperature | T _{STG} | -65~+150 | | | °C |

Electrical Ratings @T_A=25°C

| Parameter Symb | | ol | Min. | Typ. | Max. | Unit | Condit ions |
|-------------------------------|--|--------------------|----------------|------|--|------|---|
| Reverse Breakdown Voltage | SD101AW SD101BW SD101CW | V _{(BR)R} | 60 50 40 | | | V | I _R =10μA I _R =10μA I _R =10μA |
| Forward voltage | SD101AW SD101BW SD101CW SD101AW SD101BW SD101CW | V _F | | | 0.41 0.40 0.39 1.00 0.95 0.90 | V | I _F =1.0mA I _F =1.0mA I _F =1.0mA I _F =15mA I _F =15mA I _F =15mA |
| Reverse current | SD101AW SD101BW SD101CW | I _{RM} | | | 0.2 | μA | V _R =50V V _R =40V V _R =30V |
| Capacitance between terminals | SD101AW SD101BW SD101CW | C _T | | | 2.0 2.1 2.2 | pF | V _R =0V,f=1.0MHz |
| Reverse Recovery Time | | t _{rr} | | | 1. 0 | ns | I _F =I _R =5mA I _{rr} =0.1X I _R , R _L =100Ω |

